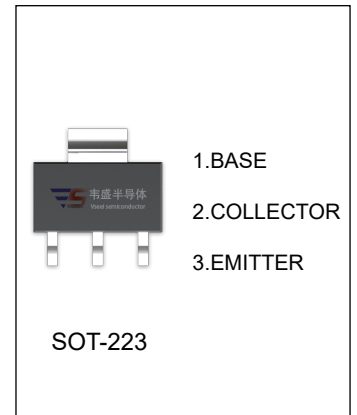


D882 TRANSISTOR (NPN)

FEATURES

- Power Dissipation:1.5W
- Low Collector-emitter Saturation Voltage



MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	3	A
P_C	Collector Dissipation	1.25	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\ \mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\ \text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\ \mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\ \text{V}, I_E=0$			1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=30\ \text{V}, I_B=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=1\text{A}$	60		400	
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=100\text{mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}, I_B=0.2\text{A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{A}, I_B=0.2\text{A}$			1.5	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=0.1\text{A}$ $f=10\text{MHz}$	50			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

